

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	81385	(specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 12:49
L2	79	@ad<"20030728" and (blister or bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) with (depth or deep or deepness deepening or deepen or range or ranging or dimension or length\$4 or thinner or thinning or thinned ot thin or thickness or thicker or thick or mill or milling or milled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 12:49
L3	64	@ad<"20030728" and (blister or bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) with (depth or deep or deepness deepening or deepen or thinner or thinning or thinned ot thin or thickness or thicker or thick or mill or milling or milled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 12:50

L4	22	@ad<"20030728" and (blister or bubble) with pattern\$4 with (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) with (depth or deep or deepness deepening or deepen or thinner or thinning or thinned ot thin or thickness or thicker or thick or mill or milling or milled)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 12:51
L5	3	@ad<"20030728" and (blister or bubble) with pattern\$4 with (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) with (depth or deep or deepness deepening or deepen or thinner or thinning or thinned ot thin or thickness or thicker or thick or mill or milling or milled) and (ion or electron) beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 12:52
L6	4	@ad<"20030728" and (blister or gas bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or gas bubble) with (depth or deep or deepness deepening or deepen or range or ranging or dimension or length\$4 or thinner or thinning or thinned ot thin or thickness or	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 14:55

		thicker or thick or mill or milling or milled)				
L7	0	@ad<"20030728" and (blister or gas bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or gas bubble) with (electron or ion) beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 15:01
L8	0	@ad<"20030728" and (blister or gas bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) with (electron or ion) beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 15:02
L9	0	@ad<"20030728" and (blister or gas bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) with (electron or ion) irradiation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 15:02
L10	0	@ad<"20030728" and (blister or gas bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) with (electron or ion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 15:02

L11	0	@ad<"20030728" and (blister or gas bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) same (electron or ion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 15:02
L12	131	@ad<"20030728" and (blister or bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) same (electron or ion)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 15:03
L13	8	@ad<"20030728" and (blister or bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) same (electron or ion) beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 15:03
L14	8	@ad<"20030728" and (blister or bubble) with pattern\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with ion with (implanter or implanting or implantation) and (blister or bubble) same (electron or ion) (irradiation or beam)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/25 15:03
S2	3600	(250/492.2).CCL.S.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/11 13:44

S3	9726	(250/492.1-492.3).CCL.S.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/11 13:44
S4	405	S3 and pattern\$4 with (two or "2") with dimension\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:45
S5	46	S3 and pattern\$4 with (two or "2") with dimension\$4 and substrate with (electron or ion) with irradiat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:46
S6	132	S3 and pattern\$4 with (two or "2") with dimension\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer)with (electron or ion) with irradiat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:47
S7	88	@ad<"20030728" and S3 and pattern\$4 with (two or "2") with dimension\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with (electron or ion) with irradiat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:48
S10	18	S3 and blister	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:49
S11	12	@ad<"20030728" and S3 and blister	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:49

S13	0	@ad<"20030728" and S3 and blister and pattern\$4 with (two or "2") with dimension\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer) with (electron or ion) with irradiat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:50
S14	0	@ad<"20030728" and S3 and blister and pattern\$4 with (two or "2") with dimension\$4 and (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:50
S15	0	@ad<"20030728" and S3 and blister and pattern\$4 with (two or "2") with dimension\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:50
S16	29	@ad<"20030728" and S3 and (blister or bubble) with pattern\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:52
S17	0	@ad<"20030728" and S3 and (blister or bubble) with ("2" or two) with dimension\$4 with pattern \$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:52
S18	0	@ad<"20030728" and S3 and (blister or bubble) same ("2" or two) with dimension\$4 with pattern \$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:52
S19	22	@ad<"20030728" and S3 and (blister or bubble or defect) same ("2" or two) with dimension\$4 with pattern\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:53

S20	15	@ad<"20030728" and S3 and (blister or bubble or defect) same ("2" or two) with dimension\$4 with pattern\$4 and (blister or bubble or defect) with (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 13:54
S21	0	@ad<"20030728" and S3 and (blister or bubble) same ("2" or two) with dimension\$4 with pattern \$4 and (blister or bubble or defect) with (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:24
S22	0	S3 and (blister or bubble) same ("2" or two) with dimension\$4 with pattern \$4 and (blister or bubble or defect) with (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:25
S23	5	S3 and (blister or bubble) and (((("2" or two) with dimension\$4 with pattern \$4 and (blister or bubble or defect) with (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:25
S24	5	S3 and (blister or bubble) and (((("2" or two) with dimension\$4) or ("2" or two)?dimension\$4) with pattern\$4 and (blister or bubble or defect) with (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:27

S25	826	(blister or bubble) and (((("2" or two) with dimension\$4) or ("2" or two)?dimension\$4) with pattern\$4 and (blister or bubble or defect) with (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:29
S26	2	S2 and (blister or bubble) and (((("2" or two) with dimension\$4) or ("2" or two)?dimension\$4) with pattern\$4 and (blister or bubble or defect) with (specimen or sample or surface or film or target or substrate or subject or workpiece or article or object or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:30
S27	0	S3 and (blister) and (((("2" or two) with dimension\$4) or ("2" or two)?dimension\$4) with pattern\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:32
S28	0	S3 and (blister) and ((((("2" or two) with dimension\$4) or ("2" or two)?dimension\$4) with pattern\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:32
S29	405	S3 and (("2" or two) with dimension\$4) or ("2" or two)?dimension\$4) with pattern\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:33
S30	2	S3 and blister with pattern \$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:33
S31	33	S3 and (bubble or blister) with pattern\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 14:34
S32	29	@ad<"20030728" and S3 and (bubble or blister) with pattern\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 15:46

S33	24	@ad<"20030728" and S3 and (bubble or blister) with pattern\$4 and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 15:50
S34	1	@ad<"20030728" and S3 and (bubble or blister) with pattern\$4 and substrate with blister	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 15:53
S35	10	@ad<"20030728" and S3 and (bubble or blister) with pattern\$4 and substrate with (bubble or blister)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 15:58
S36	1	(US-4843238-\$).did.	USPAT	ADJ	ON	2008/03/11 16:05
S37	1	@ad<"20030728" and S3 and (blister) with pattern \$4 and substrate with (blister)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 16:05
S38	1	@ad<"20030728" and S3 and (blister) same pattern \$4 and substrate with (blister)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 16:05
S40	3	@ad<"20030728" and S3 and (blister) same pattern \$4 and substrate same (blister)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 16:06
S41	4	@ad<"20030728" and S3 and (blister) same pattern \$4 and (layer or film or substrate) same (blister)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/11 18:42
S42	9726	(250/492.1-492.3).COLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/12 11:53
S43	4	@ad<"20030728" and S42 and (blister or (gas adj bubble)) same pattern \$4 and (layer or film or substrate) same (blister or (gas adj bubble))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 11:53

S44	4	@ad<"20030728" and S42 and (blister or (gas adj bubble)) and pattern \$4 and (layer or film or substrate) same (blister or (gas adj bubble))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 11:56
S45	3028	@ad<"20030728" and (blister or (gas adj bubble)) and pattern\$4 and (layer or film or substrate or wafer) same (blister or (gas adj bubble))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 12:07
S46	595	@ad<"20030728" and (blister or (gas adj bubble)) same pattern\$4 and (layer or film or substrate or wafer) same (blister or (gas adj bubble))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 12:07
S47	430	@ad<"20030728" and (blister or (gas adj bubble)) same pattern\$4 and (layer or film or substrate or wafer) with (blister or (gas adj bubble))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 12:08
S48	7	@ad<"20030728" and (blister or (gas adj bubble)) same pattern\$4 and (layer or film or substrate or wafer) with (blister or (gas adj bubble)) and (((2" or two) with dimension\$4) or ("2" or two)?dimension \$4) with pattern\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 12:09
S49	147058	("250").CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/12 12:10
S50	0	@ad<"20030728" and S49 and (blister or (gas adj bubble)) same pattern \$4 and (layer or film or substrate or wafer) with (blister or (gas adj bubble)) and (((2" or two) with dimension\$4) or ("2" or two)?dimension \$4) with pattern\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 12:10

S51	7	@ad<"20030728" and S49 and (blister or (gas adj bubble)) same pattern \$4 and (layer or film or substrate or wafer) same (blister or (gas adj bubble))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 12:10
S52	1	(US-6407399-\$).did.	USPAT	ADJ	ON	2008/03/12 12:31
S53	7	@ad<"20030728" and S49 and (blister or (gas adj bubble)) same pattern \$4 and (layer or film or substrate or wafer or resist) same (blister or (gas adj bubble))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 12:32
S54	1	@ad<"20030728" and S49 and (blister or (gas adj bubble)) same pattern \$4 and (layer or film or substrate or wafer) same (blister or (gas adj bubble)) and S52	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/12 12:34
S55	1	(US-4843238-\$).did.	USPAT	ADJ	ON	2008/03/13 11:19
S56	1	@ad<"20030728" and S63 and (blister or (gas adj bubble)) same pattern \$4 and (layer or film or substrate or wafer) same (blister or (gas adj bubble)) and S64	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 11:24
S57	2	S56 or S55	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 11:25
S58	1147	blister and ((electron or ion) adj beam)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 11:05
S59	133	blister and ((electron or ion) adj beam) and implanted	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 11:06
S60	68	blister and ((electron or ion) adj beam) and implanted and pattern	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 11:06

S61	2	("6197697").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/14 11:21
S62	6	((("6197697") or "6225193") or ("4843238")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/14 11:23
S63	3	(US-4843238-\$ or US- 6197697-\$ or US- 6225193-\$).did.	USPAT	ADJ	ON	2008/03/14 11:25
S64	3	blister and ((electron or ion) adj beam) and implanted and pattern and S63	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 11:25
S65	2	("20060211258").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/14 12:10
S66	2	blister and ((electron or ion) adj beam) and implanted and pattern and S63 AND FILM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 12:41
S67	1	blister and ((electron or ion) adj beam) and implanted and pattern and S63 AND form with FILM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 12:41
S68	1	blister and ((electron or ion) adj beam) and implanted and pattern and S63 AND (form or forming or formed) with film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 12:42
S69	1	blister and ((electron or ion) adj beam) and implanted and adsorption probability	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 12:45
S70	14	blister and ((electron or ion) adj beam) and implanted and reactiv\$4 with film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 12:46

S71	1	blister and ((electron or ion) adj beam) and implanted and reactiv\$4 with difference with film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 12:47
S72	14	blister and ((electron or ion) adj beam) and implanted and reactiv\$4 with film and chemical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 12:48
S73	6	blister and ((electron or ion) adj beam) and implanted and reactiv\$4 with film and chemical adj reaction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 12:48
S74	3	((US-4843238-\$ or US-6197697-\$ or US-6225193-\$).did.	USPAT	ADJ	ON	2008/03/14 13:42
S75	3	S63 and S74	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 13:42
S76	3	S63 or S74	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 13:42
S77	1	((US-4843238-\$).did.	USPAT	ADJ	ON	2008/03/14 13:43
S78	2	@ad<"20030728" and S63 and (blister or (gas adj bubble)) same pattern \$4 and (layer or film or substrate or wafer) same (blister or (gas adj bubble)) and S64	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 13:43
S79	2	S78 or S77	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 13:43
S80	3	S79 or S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 13:43
S81	1	((US-6407399-\$).did.	USPAT	ADJ	ON	2008/03/14 13:44
S82	1	((US-5660957-\$).did.	USPAT	ADJ	ON	2008/03/14 13:44

S83	5	S79 or S76 or S81 or S82	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 13:45
S84	30	blister and ((electron or ion) adj beam) and implanted and (xenon or argon or krypton) with ion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 14:08
S85	0	blister and ((electron or ion) adj beam) and implanted and (xenon or argon or krypton) with ion and S83	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 14:08
S86	24	@ad< "20040726" and blister and ((electron or ion) adj beam) and implanted and (xenon or argon or krypton) with ion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 14:09
S87	7	((("4,843,238") or ("6,407,399") or ("6,225,193") or ("7,038,290"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/14 14:27
S88	9	S83 or S87	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/14 14:27
S89	3	(US-4843238-\$ or US-6197697-\$ or US-6225193-\$).did.	USPAT	ADJ	ON	2008/10/23 14:52
S90	3	blister and ((electron or ion) adj beam) and implanted and pattern and S89	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 14:52
S91	3	(US-4843238-\$ or US-6197697-\$ or US-6225193-\$).did.	USPAT	ADJ	ON	2008/10/23 14:52
S92	3	S89 or S91	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 14:52
S93	1	(US-4843238-\$).did.	USPAT	ADJ	ON	2008/10/23 14:52

S94	2	@ad<"20030728" and S89 and (blister or (gas adj bubble)) same pattern \$4 and (layer or film or substrate or wafer) same (blister or (gas adj bubble)) and S90	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 14:52
S95	2	S94 or S93	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 14:52
S96	1	(US-6407399-\$).did.	USPAT	ADJ	ON	2008/10/23 14:52
S97	1	(US-5660957-\$).did.	USPAT	ADJ	ON	2008/10/23 14:52
S98	5	S95 or S92 or S96 or S97	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 14:52
S99	7	((("4,843,238") or ("6,407,399") or ("6,225,193") or ("7,038,290")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/10/23 14:52
S100	9	S98 or S99	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 14:52
S101	9	S95 or S100	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/10/23 14:52

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